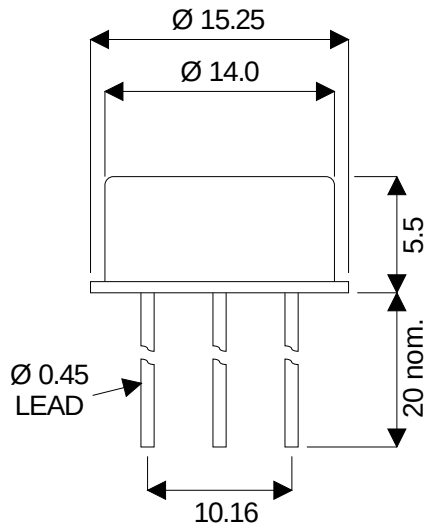
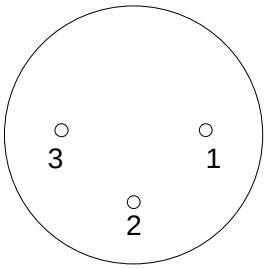
查询SMP1000G-KP供应商

SMP1000G-KP

P.I.N. PHOTODIODE

MECHANICAL DATA
Dimensions in mm.





TO-8

Pin 1 – Anode Pin 2 – Cathode Pin 3 – Case

FEATURES

- **HIGH SENSITIVITY**
- **PHOTODIODE ISOLATED FROM PACKAGE**
- **EXCELLENT LINEARITY**
- **LOW NOISE**
- **WIDE SPECTRAL RESPONSE**
- **INTEGRAL OPTICAL FILTER OPTION note 1**
- **TO8 HERMETIC METAL CAN PACKAGE**
- **EMI SCREENING MESH AVAILABLE**

Note 1 Contact Semelab Plc for filter options

DESCRIPTION

The SMP1000G-KP is a large Silicon P.I.N. photodiode incorporated in a hermetic metal can package. The electrical terminations are via two leads of diameter 0.018" on a pitch centre diameter of 0.2". The photodiode is electrically isolated from the package, which has a separate earth lead.

The larger photodiode active area provides greater sensitivity than the SMP900 range of devices, with a corresponding reduction in speed. The photodiode structure has been optimised for high sensitivity, light measurement applications. The metal can, isolated photodiode and optional screening mesh ensure a rugged device with a high degree of immunity to conducted and radiated electrical interference.

ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C unless otherwise stated)

Operating temperature range	-40°C to +70°C
Storage temperature range	-45°C to +80°C
Temperature coefficient of responsively	0.35% per °C
Temperature coefficient of dark current	x2 per 8°C rise
Reverse breakdown voltage	60V

SMP1000G-KP

CHARACTERISTICS (T_{amb}=25°C unless otherwise stated)

Characteristic	Test Conditions.	Min.	Typ.	Max.	Units
Responsively	λ at 900nm	0.45	0.55		A/W
Active Area			76.85		mm^2
Dark Current	E = 0 Dark 1V Reverse		8	9	nA
	E = 0 Dark 10V Reverse		16	38	
Breakdown Voltage	E = 0 Dark 10µA Reverse	60	80		V
Capacitance	E = 0 Dark 0V Reverse		800	735	pF
	E = 0 Dark 20V Reverse		150		
Rise Time	30V Reverse 50Ω		16		ns
NEP	900nm		$28x10^{-14}$	0.45	W/√Hz